

MGA-43013

High Linearity 728 - 756 MHz Power Amplifier Module



Data Sheet

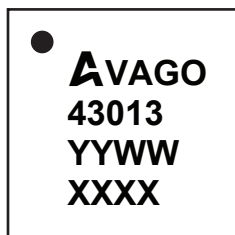
Description

Avago Technologies' MGA-43013 is a fully matched power amplifier for use in the (728 – 756) MHz band. High linear output power at 5 V is achieved through the use of Avago Technologies' proprietary 0.25 μm GaAs Enhancement-mode pHEMT process. MGA-43013 is housed in a miniature 5.0 mm $\times$ 5.0 mm molded chip-on-board (MCOB) module package. A detector is also included on-chip. The compact footprint coupled with high gain, high linearity and good efficiency, makes the MGA-43013 an ideal choice as a power amplifier for small cell BTS PA applications.

Applications

- Final stage high linearity amplifier for Picocell and Enterprise Femtocell PA targeted for small cell BTS downlink applications.

Component Image



TOP VIEW

5.0 $\times$ 5.0 $\times$ 0.9 mm Package Outline

Notes:

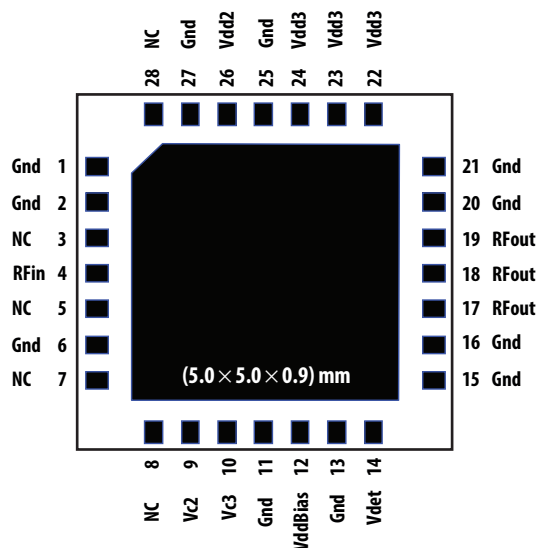
Package marking provides orientation and identification

"43013" = Device part number

"YYWW" = Year and work week

"XXXX" = Assembly lot number

Pin Configuration



Features

- High linearity performance: Max. -48 dBc ACLR1 ^[1] at 27 dBm linear output power (biased with 5 V supply)
- High Gain: 33.5 dB
- Good efficiency
- Fully matched
- Built-in detector
- GaAs E-pHEMT Technology ^[2]
- Low-cost small package size: (5.0 $\times$ 5.0 $\times$ 0.9) mm
- MSL3
- Lead-free/Halogen-free/RoHS compliance

Specifications

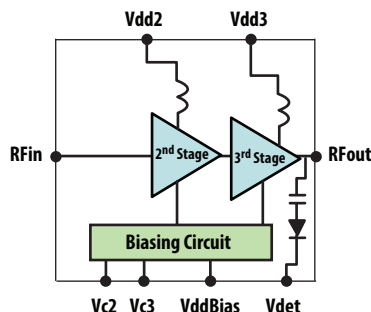
751 MHz; 5.0 V, Idqtotal = 259 mA (typ), LTE DL 10MHz 50 RB ETM 1.1 downlink signal

- PAE : 16.5%
- 27 dBm linear P_{out} @ ACLR1 = -48 dBc ^[1]
- 33.5 dB Gain
- Detector range : 20 dB

Notes:

- LTE DL 10 MHz 50 RB ETM 1.1
- Enhancement mode technology employs positive V_{GS}, thereby eliminating the need of negative gate voltage associated with conventional depletion mode devices.

Functional Block Diagram



Attention: Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model = 60 V

ESD Human Body Model = 400 V

Refer to Avago Application Note A004R:

Electrostatic Discharge, Damage and Control.

Absolute Maximum Rating^[1] $T_A = 25\text{ }^{\circ}\text{C}$

Symbol	Parameter	Units	Absolute Max.
V_{dd}, V_{ddBias}	Supply voltages, bias supply voltage	V	6
V_c	Control Voltage	V	(Vdd)
$P_{in,max}$	CW RF Input Power	dBm	20
P_{diss}	Total Power Dissipation ^[3]	W	4.9
T_j	Junction Temperature	$^{\circ}\text{C}$	150
T_{STG}	Storage Temperature	$^{\circ}\text{C}$	-65 to 150

Thermal Resistance^[2,3]

$$\theta_{jc} = 15.7\text{ }^{\circ}\text{C/W}$$

Notes:

1. Operation of this device in excess of any of these limits may cause permanent damage.
2. Thermal resistance measured using Infra-Red Measurement Technique.
3. Board temperature (T_B) is $25\text{ }^{\circ}\text{C}$, for $T_B > 73\text{ }^{\circ}\text{C}$ derate the device power at 63 mW per $^{\circ}\text{C}$ rise in Board (package belly) temperature.

Electrical Specifications

$T_A = 25\text{ }^{\circ}\text{C}$, $V_{dd} = V_{ddBias} = 5.0\text{ V}$, $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$, $I_{dqttotal} = 259\text{ mA}$, RF performance at 751 MHz, LTE DL 10 MHz 50 RB ETM 1.1 downlink signal operation, unless otherwise stated

Symbol	Parameter and Test Condition	Frequency (MHz)	Units	Min.	Typ.	Max.
V_{dd}	Supply Voltage		V	-	5.0	-
$I_{dqttotal}$	Quiescent Supply Current		mA	-	259	-
Gain	Gain		dB	31	33.5	-
OP1dB	Output Power at 1 dB Gain Compression		dBm	-	36	-
ACLR1 @ $P_{out} = 27\text{ dBm}$	LTE DL 10MHz 50RB ETM1.1 downlink signal	733	dBc	-	-47	-
		739			-47	
		751			-48	
PAE	Power Added Efficiency		%	14	16.5	-
S11	Input Return Loss, 50 Ω source		dB	-	14	-
DetR	Detector RF dynamic range		dB	-	20	-
2fo	2fo Harmonics (LTE DL 10MHz 50RB ETM1.1 downlink signal)		dBc	-	-35	-

Product Consistency Distribution Charts [4]

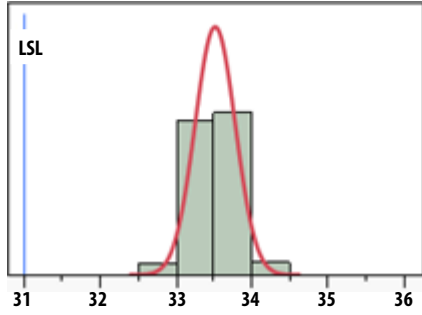


Figure 1. Gain at $P_{out} = 27$ dBm, LSL = 31 dB, nominal = 33.5 dB

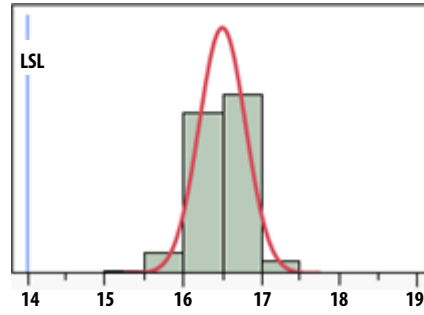


Figure 2. PAE at $P_{out} = 27$ dBm, LSL = 14%, nominal = 16.5%

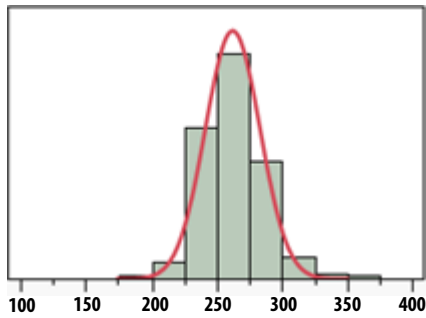


Figure 3. I_{dqtot} , Nominal = 259 mA

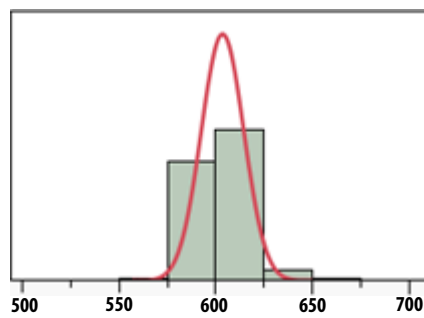


Figure 4. I_{dd_Total} at $P_{out} = 27$ dBm, nominal = 602 mA

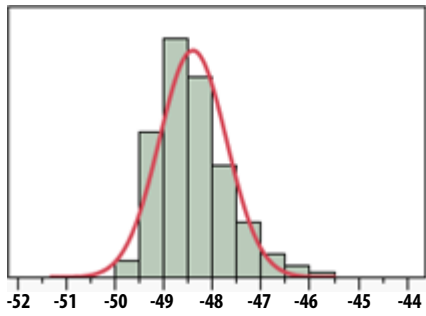


Figure 5. ACLR1 at $P_{out} = 27$ dBm, nominal = -48.5 dBc

Note:

4. Distribution data sample size is 3365 samples taken from three wafer lots. $T_A = 25$ °C, $V_{dd} = V_{ddBias} = 5.0$ V, $V_{c2} = 3$ V, $V_{c3} = 2.6$ V, RF performance at 751 MHz, unless otherwise stated. Future wafers allocated to this product may have nominal values anywhere between the upper and lower limits.

MGA-43013 typical over-temperature performance at $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$ ($V_{dd} = V_{ddBias} = 5\text{ V}$) as shown in Figure 27 and $V_{c2} = 2.9\text{ V}$, $V_{c3} = 2.3\text{ V}$ ($V_{dd} = V_{ddBias} = 5.5\text{ V}$), unless otherwise stated

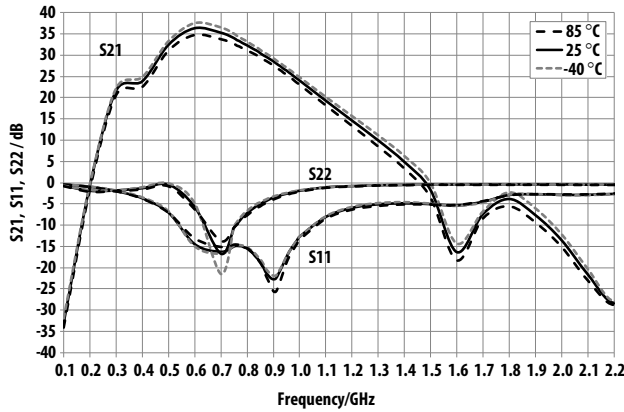


Figure 6. Small-signal performance Over-temperature
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

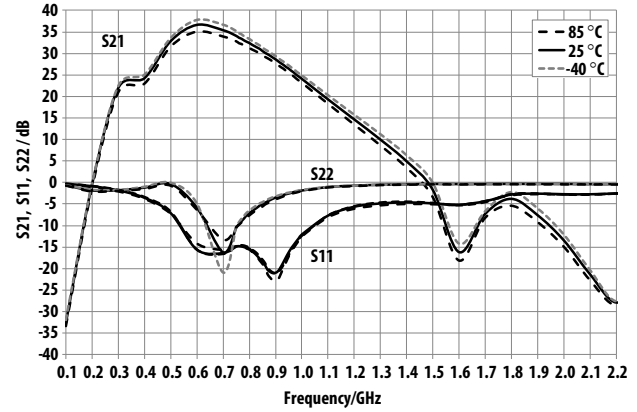


Figure 7. Small-signal performance Over-temperature
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

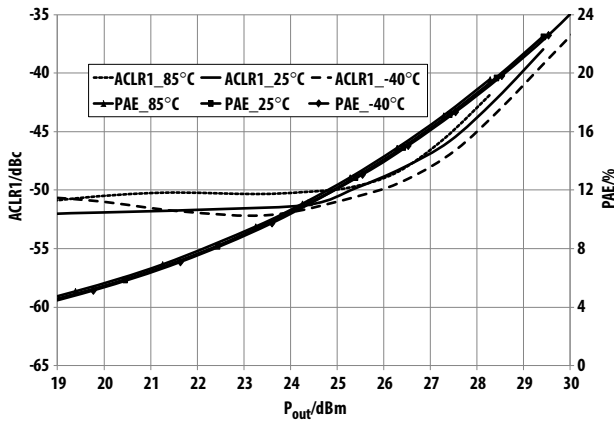


Figure 8. Over-temperature ACLR1, PAE vs. P_{out} @ 733 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

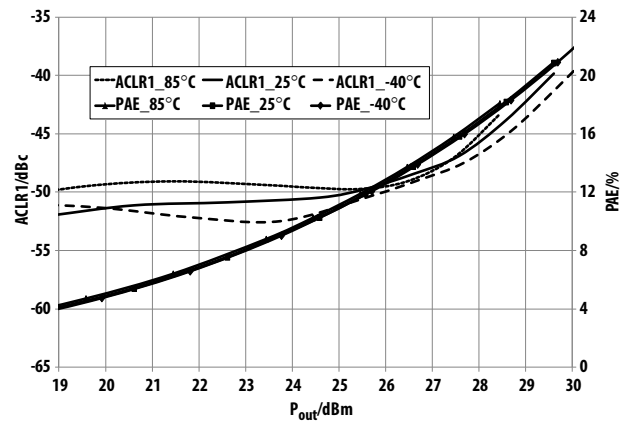


Figure 9. Over-temperature ACLR1, PAE vs. P_{out} @ 733 MHz
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

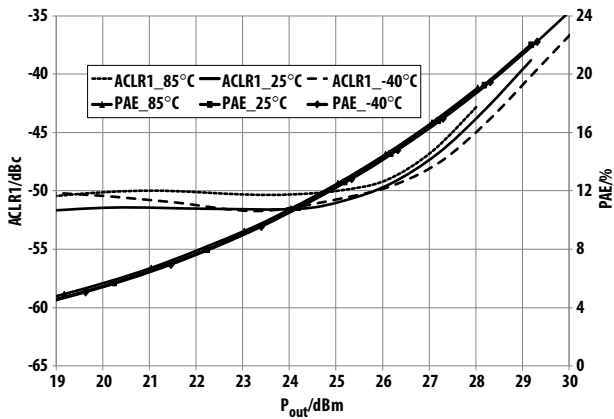


Figure 10. Over-temperature ACLR1, PAE vs. P_{out} @ 739 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

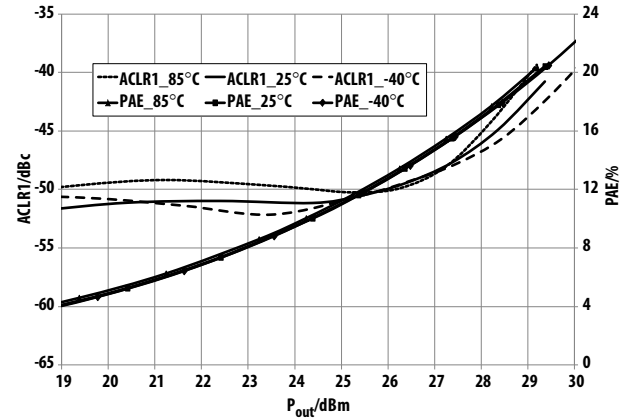


Figure 11. Over-temperature ACLR1, PAE vs. P_{out} @ 739 MHz
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

MGA-43013 typical over-temperature performance at $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$ ($V_{dd} = V_{ddBias} = 5\text{ V}$) as shown in Figure 27 and $V_{c2} = 2.9\text{ V}$, $V_{c3} = 2.3\text{ V}$ ($V_{dd} = V_{ddBias} = 5.5\text{ V}$), unless otherwise stated

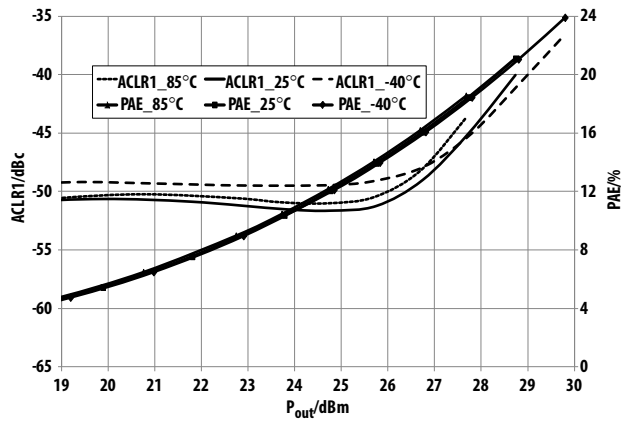


Figure 12. Over-temperature ACLR1, PAE vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

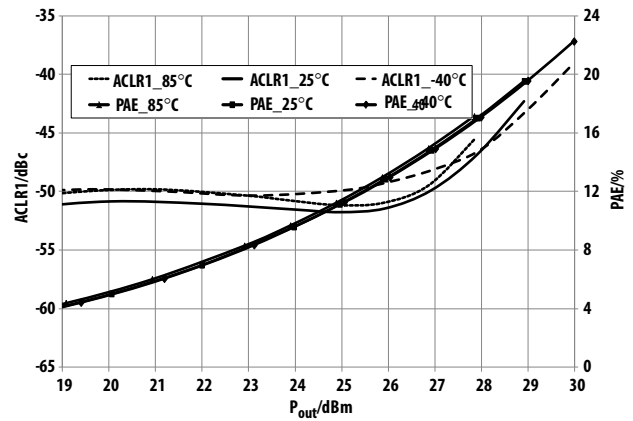


Figure 13. Over-temperature ACLR1, PAE vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

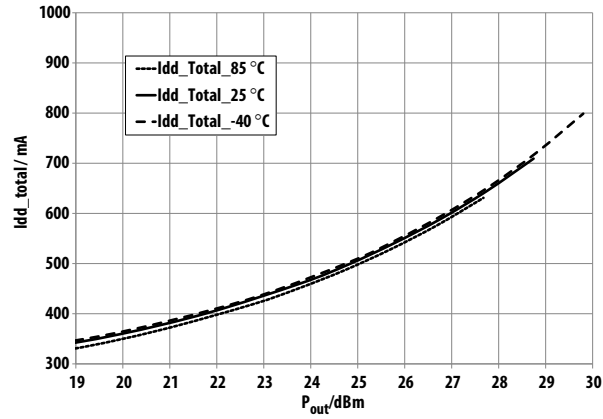


Figure 14. Over-temperature I_{dd_Total} vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

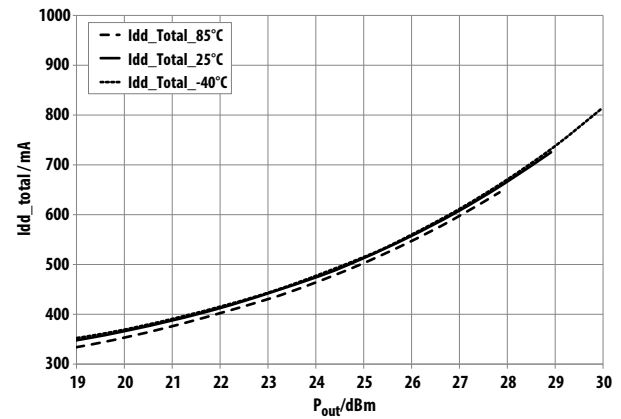


Figure 15. Over-temperature I_{dd_Total} vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

MGA-43013 typical over-temperature performance at $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$ ($V_{dd} = V_{ddBias} = 5\text{ V}$) as shown in Figure 27 and $V_{c2} = 2.9\text{ V}$, $V_{c3} = 2.3\text{ V}$ ($V_{dd} = V_{ddBias} = 5.5\text{ V}$), unless otherwise stated

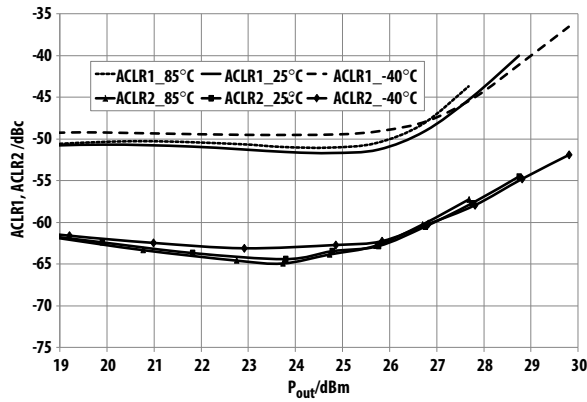


Figure 16. Over-temperature ACLR1, ACLR2 P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

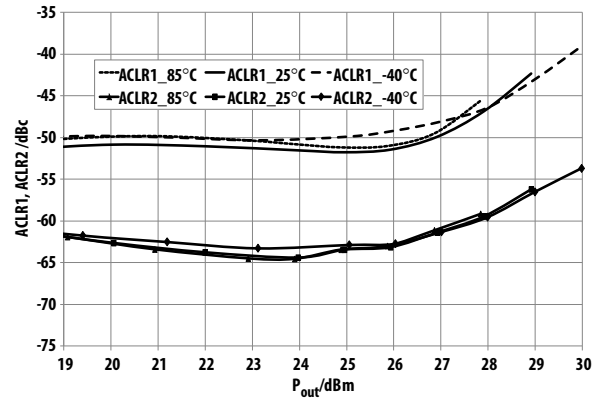


Figure 17. Over-temperature ACLR1, ACLR2 vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.5\text{ V}$ operating voltage

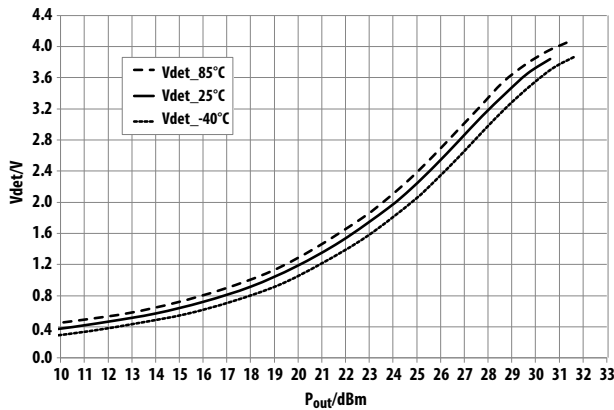


Figure 18. Over-temperature V_{det} vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

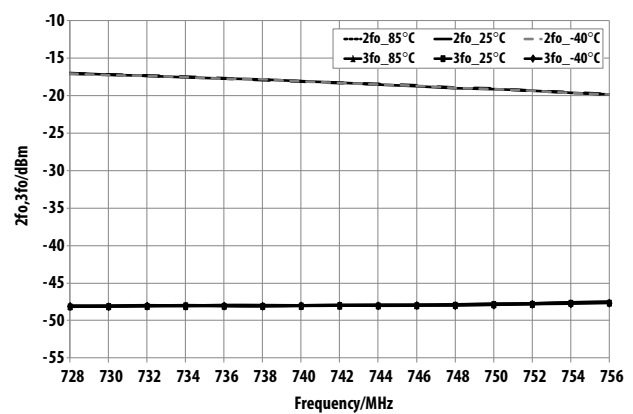


Figure 19. Over-temperature 2nd, 3rd Harmonics vs. Freq at $P_{out} = 27\text{ dBm}$,
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

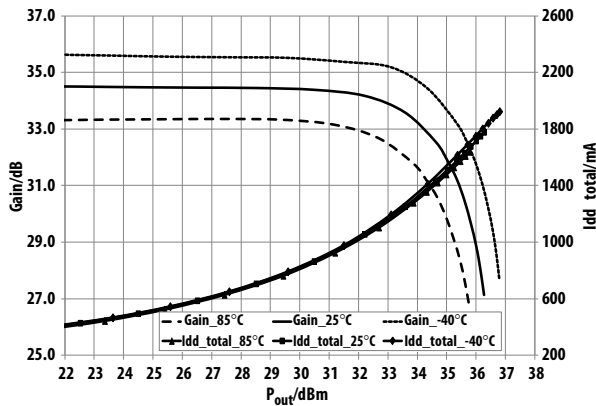


Figure 20. Over-temperature Gain, I_{dd_Total} vs. P_{out} @ 733 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

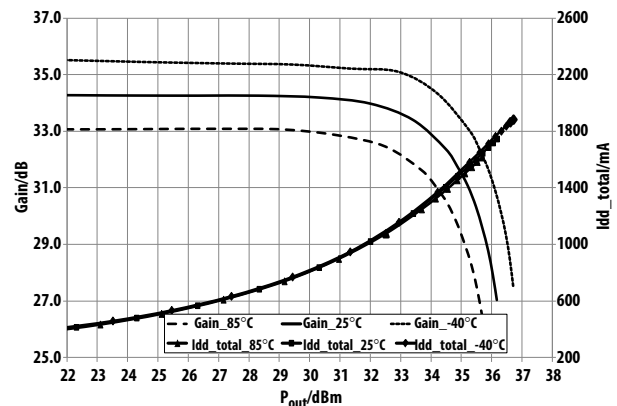


Figure 21. Over-temperature Gain, I_{dd_Total} vs. P_{out} @ 739 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ voltage

MGA-43013 typical over-temperature performance at $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$ ($V_{dd} = V_{ddBias} = 5\text{ V}$) as shown in Figure 27 and $V_{c2} = 2.9\text{ V}$, $V_{c3} = 2.3\text{ V}$ ($V_{dd} = V_{ddBias} = 5.5\text{ V}$), unless otherwise stated

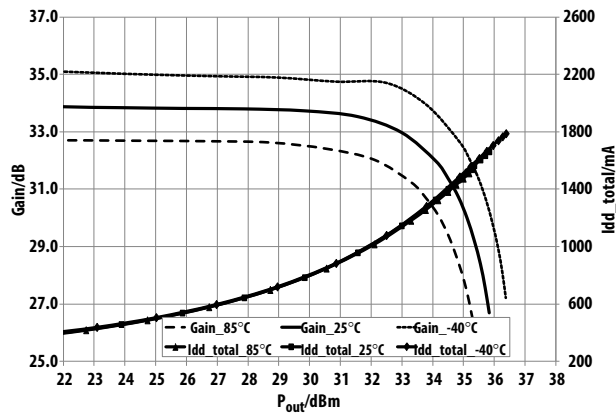


Figure 22. Over-temperature Gain, Idd_Total vs. P_{out} @ 751 MHz
 $V_{dd} = V_{ddBias} = 5.0\text{ V}$ operating voltage

MGA-43013 typical LTE DL 10 MHz 50 RB ETM 1.1 Spectrum Emission Mask performance at $V_{dd} = V_{ddBias} = 5.0\text{ V}$, $V_{c2} = 3\text{ V}$, $V_{c3} = 2.6\text{ V}$, unless otherwise stated

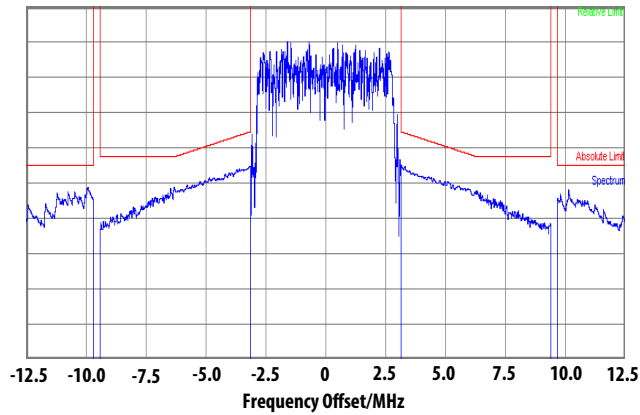


Figure 23. SEM at $P_{out} = 31\text{ dBm}$ @ 733 MHz

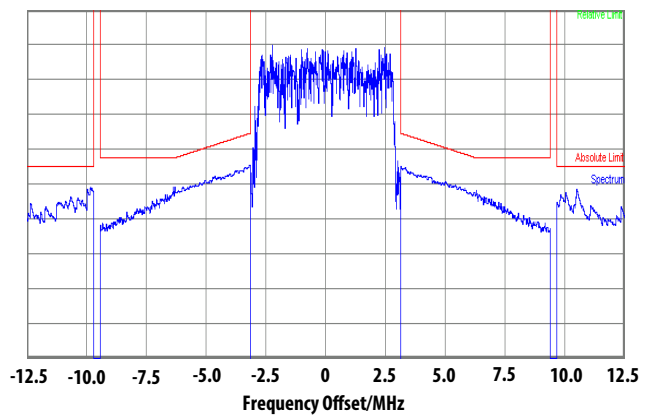


Figure 24. SEM at $P_{out} = 31\text{ dBm}$ @ 739 MHz

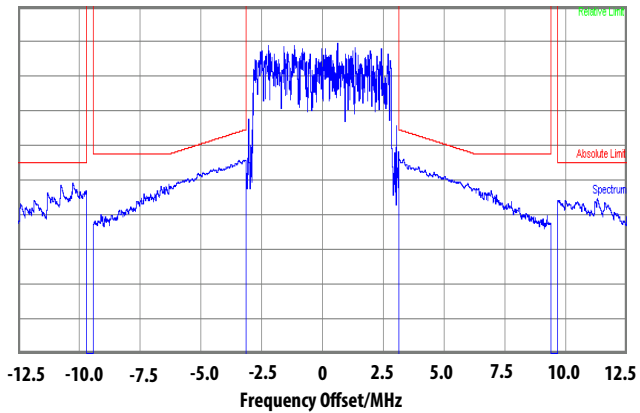


Figure 25. SEM at $P_{out} = 31\text{ dBm}$ @ 751 MHz

S-Parameter^[5] (Vdd = VddBias = 5.0 V, Vc2 = 3 V, Vc3 = 2.6 V, T_A = 25 °C, 50 Ω)

Freq (GHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
0.1	-0.355	160.899	-31.44	1.288	-52.928	104.298	-0.834	172.431
0.2	-0.673	139.88	-1.028	-45.497	-62.974	24.319	-1.731	168.289
0.3	-1.354	113.974	20.626	-148.403	-62.389	-134.989	-1.486	-179.014
0.4	-3.001	76.971	23.98	105.855	-66.44	-135.611	-0.802	162.018
0.5	-7.047	7.635	32.028	82.124	-66.234	-42.776	-0.338	154.451
0.6	-18.752	-94.341	36.398	-24.156	-52.697	-175.508	-4.935	123.769
0.65	-24.535	-116.513	36.278	-68.029	-51.737	136.001	-10.466	124.306
0.66	-25.141	-112.66	36.154	-76.263	-52.16	128.96	-11.904	127.93
0.67	-24.484	-107.406	36.009	-84.231	-50.564	130.612	-13.425	134.675
0.68	-23.588	-103.761	35.834	-92.057	-52.025	123.248	-14.788	144.632
0.69	-22.564	-102.535	35.636	-99.707	-52.512	116.999	-15.749	158.087
0.70	-21.511	-103.368	35.418	-107.194	-51.653	111.879	-16.043	173.517
0.71	-20.503	-105.12	35.178	-114.562	-51.878	102.079	-15.544	-171.962
0.72	-19.536	-109.06	34.927	-121.697	-50.854	103.77	-14.456	-161.408
0.73	-18.853	-112.625	34.656	-128.669	-49.767	98.627	-13.243	-153.92
0.74	-18.249	-116.591	34.396	-135.546	-49.435	87.965	-12.088	-148.64
0.75	-17.725	-121.092	34.122	-142.277	-49.933	76.574	-11.024	-145.127
0.76	-17.369	-125.833	33.771	-148.75	-50.981	71.436	-10.032	-143.096
0.77	-17.141	-130.362	33.456	-155.196	-50.448	71.661	-9.153	-142.035
0.78	-17.029	-134.692	33.127	-161.468	-51.416	68.725	-8.401	-141.457
0.79	-17.011	-139.192	32.791	-167.652	-52.043	66.924	-7.712	-141.196
0.80	-17.099	-143.665	32.447	-173.75	-51.895	62.79	-7.086	-141.214
0.81	-17.326	-147.579	32.091	-179.715	-51.706	49.045	-6.546	-141.539
0.82	-17.713	-150.868	31.733	174.51	-51.655	42.253	-6.03	-142.06
0.83	-18.269	-154.108	31.363	168.817	-50.662	36.956	-5.583	-142.601
0.84	-18.962	-156.806	30.98	163.178	-50.518	31.651	-5.17	-143.213
0.85	-19.803	-158.849	30.59	157.626	-51.34	28.663	-4.789	-143.896
0.86	-20.839	-160.31	30.199	152.219	-52.375	31.276	-4.448	-144.619
0.87	-22.16	-160.016	29.797	146.888	-51.749	14.743	-4.124	-145.52
0.88	-23.719	-156.712	29.395	141.645	-51.383	14.104	-3.834	-146.425
0.89	-25.5	-148.756	28.985	136.507	-51.346	12.416	-3.564	-147.309
0.90	-27.188	-134.535	28.564	131.469	-51.543	7.359	-3.314	-148.173
0.95	-20.608	-67.168	26.381	107.544	-53.081	-5.71	-2.31	-152.629
1.0	-14.278	-68.437	24.115	86.219	-56.217	-38.52	-1.646	-156.822
1.1	-8.797	-87.737	19.53	49.754	-58.556	-66.677	-0.885	-163.901
1.2	-6.323	-108.921	14.868	17.918	-61.599	-78.028	-0.526	-169.849
1.3	-5.214	-125.38	10.143	-10.899	-62.654	-105.222	-0.353	-174.627
1.4	-4.829	-137.802	4.961	-38.688	-62.275	-143.392	-0.248	-178.523
1.5	-4.982	-145.809	-2.066	-66.498	-64.696	-178.348	-0.182	178.012
1.6	-5.131	-147.151	-17.062	-49.283	-60.97	144.122	-0.158	174.823
1.7	-4.166	-144.989	-6.543	26.964	-62.539	158.517	-0.177	172.046
1.8	-2.519	-153.421	-3.589	-32.511	-71.298	114.408	-0.164	169.395

S-Parameter^[5] (Vdd = VddBias = 5.0 V, Vc2 = 3 V, Vc3 = 2.6 V, TA=25 °C, 50 Ω) cont.

Freq (GHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
1.9	-2.34	-163.567	-7.159	-76.259	-60.219	118.865	-0.152	166.664
2.0	-2.457	-169.222	-12.686	-105.145	-58.989	128.397	-0.149	163.852
2.1	-2.409	-173.062	-19.789	-121.336	-62.194	92.489	-0.139	160.95
2.2	-2.219	-176.184	-28.508	-100.025	-62.194	106.657	-0.155	157.821
2.3	-1.915	-179.949	-25.832	-54.447	-62.829	81.052	-0.179	154.426
2.4	-1.548	174.507	-18.971	-79.725	-68.022	113.86	-0.203	150.515
2.5	-1.95	169.971	-20.041	-174.686	-58.067	85.64	-0.248	145.976
2.6	-1.774	167.746	-18.284	124.246	-57.929	81	-0.349	140.025
2.7	-1.631	163.259	-5.855	47.646	-51.442	36.301	-0.965	132.17
2.8	-1.755	161.177	-3.183	-76.71	-59.276	-56.859	-1.188	127.113
2.9	-1.653	158.351	-6.914	153.255	-61.02	100.046	-1.736	128.7
3.0	-1.538	155.46	-22.08	98.288	-57.85	42.785	-1.035	111.504
3.5	-1.322	141.65	-17.872	22.299	-57.609	-35.372	-2.144	-94.789
4.0	-1.267	131.161	-42.932	-133.036	-71.604	-153.261	-0.358	-160.398
4.5	-1.35	122.067	-56.173	36.758	-67.228	102.214	-0.17	-175.537
5.0	-1.602	110.325	-66.918	-96.396	-72.144	101.01	-0.104	176.735
5.5	-2.191	88.118	-62.286	-128.67	-67.875	130.204	-0.108	170.559
6.0	-2.562	67.873	-60.672	-138.942	-64.112	100.455	-0.146	164.429
7.0	-1.387	39.826	-48.48	9.994	-67.568	-4.299	-0.35	151.674
8.0	-1.653	31.312	-44.523	-89.309	-68.756	138.891	-0.35	138.008
9.0	-3.287	5.787	-42.755	144.041	-61.954	110.497	-0.094	127.867
10.0	-3.471	-55.343	-47.43	87.431	-57.374	90.638	-0.47	120.072
11.0	-2.827	-104.854	-46.516	50.459	-54.803	31.06	-1.449	113.045
12.0	-3.59	-152.852	-42.637	2.35	-60.129	-115.67	-0.727	94.311
13.0	-5.839	154.742	-39.08	-88.445	-58.841	-104.157	-0.834	62.45
14.0	-18.964	-176.045	-40.759	109.569	-50.763	50.502	-1.294	25.88
15.0	-4.422	160.804	-60.914	-121.949	-43.659	-32.968	-2.417	-10.161
16.0	-1.443	127.588	-38.159	105.708	-47.648	-113.077	-4.933	-73.351
17.0	-2.063	105.554	-30.527	-101.519	-38.785	-145.514	-14.138	-100.468
18.0	-3.483	62.786	-35.413	134.42	-42.874	115.741	-7.145	-59.924
19.0	-3.865	38.428	-42.134	88.917	-45.644	134.054	-4.922	-101.388
20.0	-3.113	34.181	-44.385	4.926	-51.035	59.868	-6.044	-90.49

Note:

5. S-parameter is measured with de-embedded reference plane at DUT RFin and RFout pins.

S-Parameter^[5] (Vdd = VddBias = 5.5 V, Vc2 = 2.9 V, Vc3 = 2.3 V, T_A=25 °C, 50 Ω)

Freq (GHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
0.1	-0.355	160.921	-31.244	0.426	-59.056	-141.277	-0.841	172.412
0.2	-0.68	139.916	-0.655	-45.097	-58.093	148.034	-1.746	168.181
0.3	-1.351	114.015	21.087	-148.054	-70.545	-32.978	-1.518	-178.51
0.4	-3.003	76.981	24.469	105.423	-62.968	-112.645	-0.777	162.138
0.5	-7.245	7.005	32.56	80.99	-69.41	-52.357	-0.289	154.286
0.6	-21.054	-94.875	36.757	-26.503	-51.217	179.867	-5.114	123.985
0.65	-28.556	-98.713	36.527	-70.178	-51.902	143.057	-10.634	126.441
0.66	-28.01	-88.514	36.39	-78.345	-51.293	142.165	-12.064	130.736
0.67	-26.419	-83.965	36.23	-86.24	-50.245	136.933	-13.421	138.202
0.68	-24.886	-82.922	36.046	-93.991	-50.194	126.365	-14.539	148.561
0.69	-23.337	-84.612	35.838	-101.575	-50.503	119.2	-15.258	161.253
0.70	-21.913	-87.857	35.611	-108.999	-50.871	112.858	-15.417	174.908
0.71	-20.78	-91.222	35.366	-116.289	-51.169	98.483	-14.949	-172.47
0.72	-19.805	-96.941	35.109	-123.328	-52.082	101.319	-13.97	-162.471
0.73	-18.992	-101.997	34.834	-130.232	-52.781	94.207	-12.896	-155.413
0.74	-18.392	-106.94	34.572	-137.044	-52.508	85.471	-11.85	-150.354
0.75	-17.949	-112.031	34.299	-143.713	-51.58	78.257	-10.872	-146.864
0.76	-17.566	-117.325	33.956	-150.136	-50.864	72.125	-9.967	-144.738
0.77	-17.389	-122.195	33.638	-156.521	-50.292	56.814	-9.138	-143.645
0.78	-17.3	-127.038	33.311	-162.773	-49.755	64.066	-8.39	-142.916
0.79	-17.311	-131.366	32.976	-168.927	-50.263	61.392	-7.732	-142.419
0.80	-17.43	-135.217	32.633	-174.985	-51.141	48.115	-7.146	-142.198
0.81	-17.662	-138.954	32.282	-179.073	-50.477	42.836	-6.602	-142.373
0.82	-18.085	-142.366	31.925	-173.308	-50.695	47.616	-6.101	-142.777
0.83	-18.638	-145.038	31.559	-167.647	-51.213	43.359	-5.653	-143.154
0.84	-19.319	-146.952	31.181	-162.037	-51.608	34.804	-5.229	-143.615
0.85	-20.138	-147.912	30.794	-156.49	-51.653	27.502	-4.839	-144.209
0.86	-21.111	-147.607	30.4	-151.057	-51.302	27.146	-4.506	-144.944
0.87	-22.247	-144.79	29.997	-145.746	-50.545	26.442	-4.183	-145.832
0.88	-23.481	-139.057	29.593	-140.493	-51.618	20.333	-3.883	-146.63
0.89	-24.562	-128.921	29.184	-135.348	-52.379	13.798	-3.61	-147.446
0.90	-25.146	-114.927	28.766	-130.306	-52.514	10.563	-3.362	-148.283
0.95	-18.891	-70.252	26.577	-106.356	-54.066	-11.845	-2.336	-152.597
1.0	-13.485	-71.46	24.299	-84.995	-56.899	-33.034	-1.66	-156.701
1.1	-8.444	-89.696	19.689	-48.574	-57.154	-48.972	-0.881	-163.818
1.2	-6.114	-110.276	14.995	-16.786	-60.905	-91.638	-0.527	-169.834
1.3	-5.056	-126.461	10.244	-11.87	-61.957	-124.268	-0.344	-174.639
1.4	-4.712	-138.645	5.034	-39.455	-60.057	-154.796	-0.244	-178.529
1.5	-4.876	-146.55	-2.007	-66.99	-63.765	-168.166	-0.182	178.015
1.6	-5.062	-148.006	-16.977	-49.038	-70.82	123.355	-0.157	174.849
1.7	-4.133	-145.884	-6.416	26.304	-63.323	168.823	-0.172	172.056
1.8	-2.513	-154.074	-3.529	-32.863	-66.593	161.509	-0.164	169.404

S-Parameter^[5] (Vdd = VddBias = 5.5 V, Vc2 = 2.9 V, Vc3 = 2.3 V, TA=25 °C, 50 Ω) Cont.

Freq (GHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	S22 (dB)	S22 (ang)
1.9	-2.337	-163.993	-7.116	-76.35	-68.941	139.207	-0.149	166.691
2.0	-2.446	-169.628	-12.596	-104.855	-67.804	134.671	-0.147	163.904
2.1	-2.416	-173.397	-19.68	-120.692	-58.891	94.506	-0.139	161.034
2.2	-2.226	-176.47	-28.348	-98.788	-61.505	136.493	-0.15	157.861
2.3	-1.916	179.886	-25.506	-55.071	-66.732	36.482	-0.173	154.49
2.4	-1.53	174.257	-18.849	-80.281	-63.539	89.206	-0.196	150.578
2.5	-1.948	169.775	-19.915	-174.355	-62.576	95.689	-0.24	146.016
2.6	-1.777	167.552	-18.034	124.397	-54.279	86.492	-0.334	140.069
2.7	-1.628	163.088	-5.649	47.622	-50.57	37.232	-0.955	132.224
2.8	-1.759	161	-2.987	-76.428	-60.106	-73.908	-1.182	127.134
2.9	-1.658	158.182	-6.751	153.594	-61.192	114.97	-1.717	128.691
3.0	-1.542	155.347	-21.902	99.011	-58.067	61.654	-1.023	111.465
3.5	-1.329	141.535	-17.66	22.178	-59.619	-35.077	-2.14	-94.818
4.0	-1.275	131.158	-43.136	-134.279	-69.215	29.025	-0.338	-160.499
4.5	-1.354	122.091	-56.788	27.458	-69.182	75.91	-0.157	-175.661
5.0	-1.593	110.321	-69.859	-144.892	-71.595	70.617	-0.092	176.779
5.5	-2.169	88.01	-63.441	-86.408	-72.66	-176.71	-0.092	170.755
6.0	-2.575	67.391	-58.769	-140.71	-65.318	99.708	-0.132	164.589
7.0	-1.411	40.073	-48.839	12.85	-65.308	28.39	-0.311	151.27
8.0	-1.67	31.565	-45.155	-88.975	-72.126	100.025	-0.296	137.594
9.0	-3.36	5.825	-42.395	142.976	-61.051	121.156	-0.085	128.17
10.0	-3.552	-54.909	-46.741	87.537	-56.599	105.707	-0.561	119.235
11.0	-2.863	-104.198	-47.844	51.858	-56.511	34.143	-1.747	111.705
12.0	-3.654	-151.874	-42.841	1.013	-59.274	-112.558	-0.784	94.571
13.0	-5.806	155.954	-39.422	-89.244	-58.696	-127.726	-0.91	63.243
14.0	-19.616	178.527	-40.831	110.89	-49.754	50.315	-1.45	27.58
15.0	-4.624	160.575	-55.905	-101.656	-44.806	-33.658	-2.454	-9.947
16.0	-1.475	128.243	-37.705	113.423	-47.565	-116.474	-4.948	-71.917
17.0	-2.062	106.317	-30.305	-97.016	-38.839	-141.969	-14.295	-101.219
18.0	-3.464	64.155	-35.01	136.292	-43.16	117.213	-7.172	-59.553
19.0	-3.855	39.571	-42.274	88.072	-45.6	134.029	-4.911	-100.228
20.0	-3.099	35.09	-44.02	6.838	-49.794	64.537	-6.113	-90.074

Note:

5. S-parameter is measured with de-embedded reference plane at DUT RFin and RFout pins.

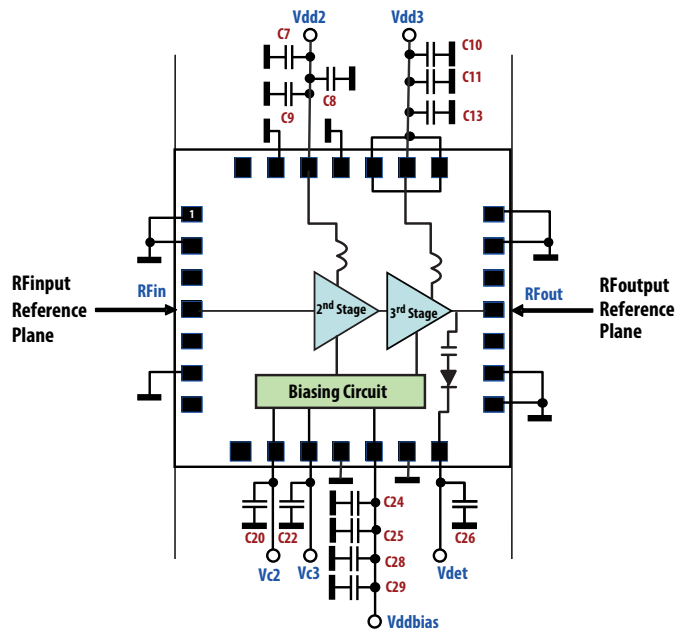
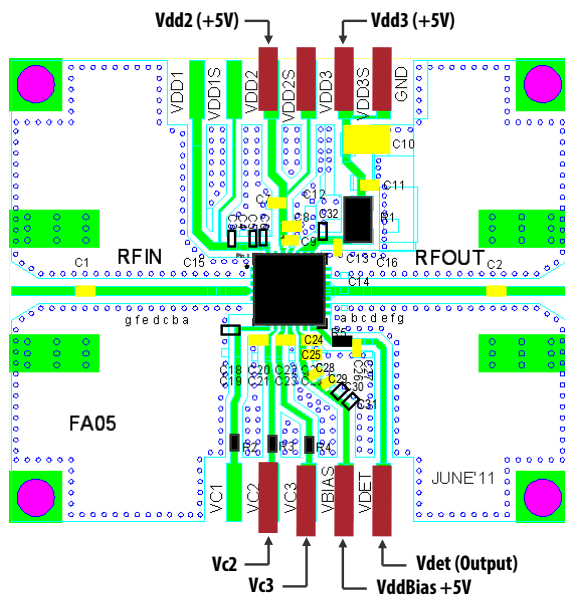


Figure 26. RFinput and RFoutput Reference Plane

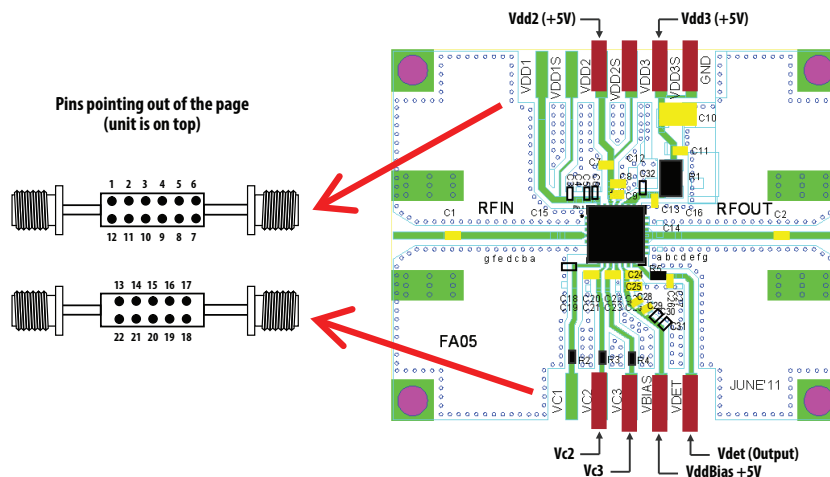
Demonstration Board Top View (Vdd = VddBias = 5.0 V, Vc2 = 3 V, Vc3 = 2.6 V)



Component	Value	Part Number
C1, C2, C20, C22	56 pF $\pm$ 5%	GRM1555C1H056JA01D
C11, C29	0.1 μ F $\pm$ 10%	GRM155R71C104KA88D
C24	82 pF $\pm$ 5%	GRM1555C1H820JA01D
C8, C25	2200 pF $\pm$ 10%	GRM155R71H222KA01D
C7, C13, C28	0.047 μ F $\pm$ 10%	GRM155R71E473KA88D
C9	12 pF $\pm$ 5%	GJM1555C1H120JB01D
C26	22 nF $\pm$ 10%	CM05X7R223K16AHF
C10	2.2 μ F $\pm$ 10%	GRM21BR71E225KA73L
R1	0 Ω	RMC1/10 JPTP
R3, R4, R5	0 Ω	RMC1/16S JPTH

Note:

For performance optimization control voltage for individual stages can be adjusted by varying R3 and R4 resistor values.



Application board pin header assignments

- Pin 1 : Vdd3 (Sense)
- Pin 2 : Vdd3 (Force)
- Pin 3 : Vdd2 (Sense)
- Pin 4 : Vdd2 (Force)
- Pin 5 : Vdd1 (Sense) – not used
- Pin 6 : Vdd1 (Force) – not used
- Pin 13 : Vc1 – not used
- Pin 14 : Vc2
- Pin 15 : Vc3
- Pin 16 : VddBias
- Pin 17 : Vdet

Other pins are grounded

Figure 27. Demonstration board application circuit for MGA-43013 module

Application Schematic

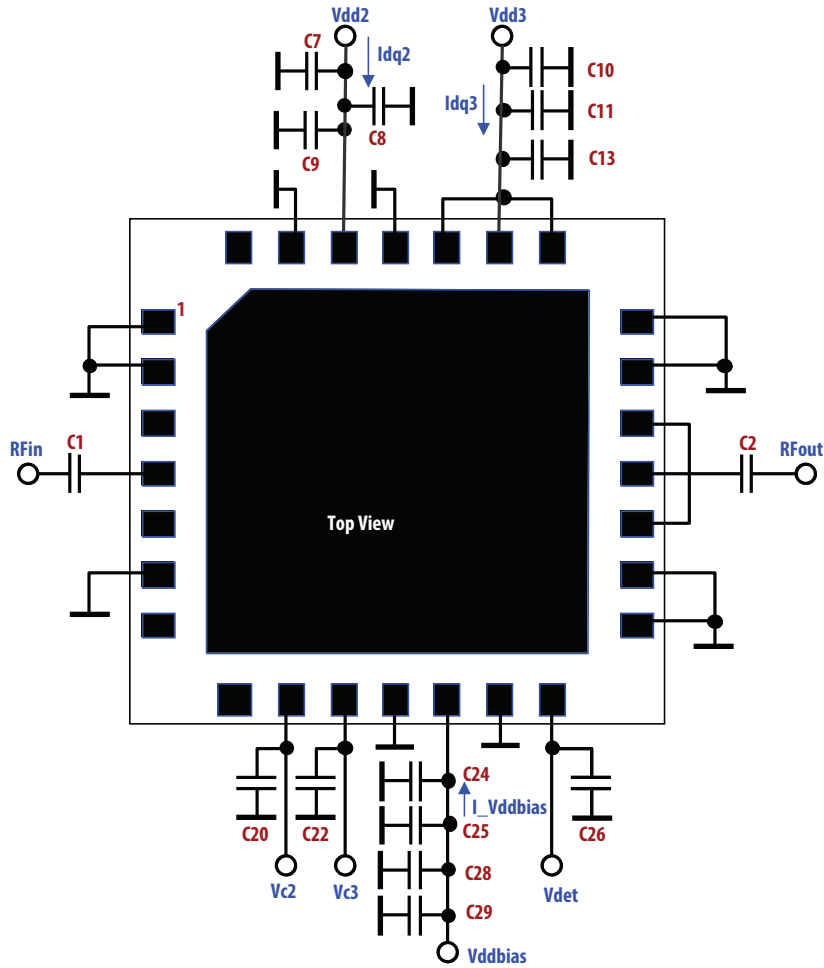


Figure 28. Application schematic in demonstration board

Notes:

1. All capacitors on supply lines are bypass capacitors.
2. $C1$ and $C2$ are RF coupling capacitors.
3. For $V_{dd} = V_{ddBias} = 5\text{ V}$, $I_{dq2} = 68\text{ mA}$, $I_{dq3} = 191\text{ mA}$, $I_{V_{ddBias}} = 14\text{ mA}$. I_{dq2} and I_{dq3} are adjusted by voltages to CMOS-compatible control pins V_{c2} and V_{c3} , respectively. These typical bias currents were obtained with V_{c2} and V_{c3} voltages in Figure 26. Adjustment of these currents enable optimum bias conditions to be achieved for best linearity and efficiency for a given modulation type.

MGA-43013 typical I_C 2, I_C 3 vs. V_C performance, unless otherwise stated

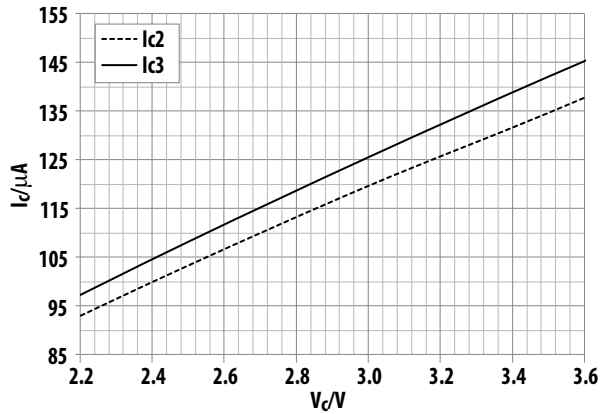


Figure 29. I_C vs. V_C at $V_{DD} = V_{DD\text{Bias}} = 5.0$ V

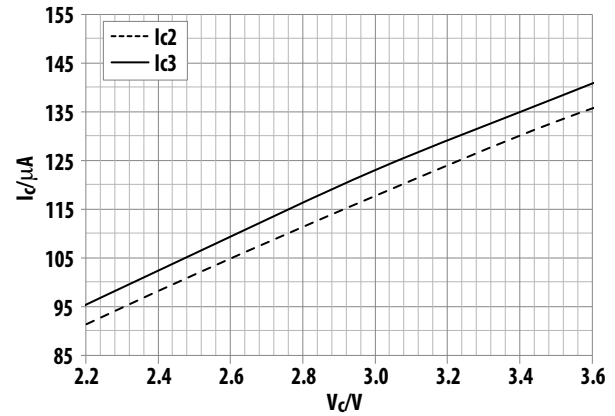
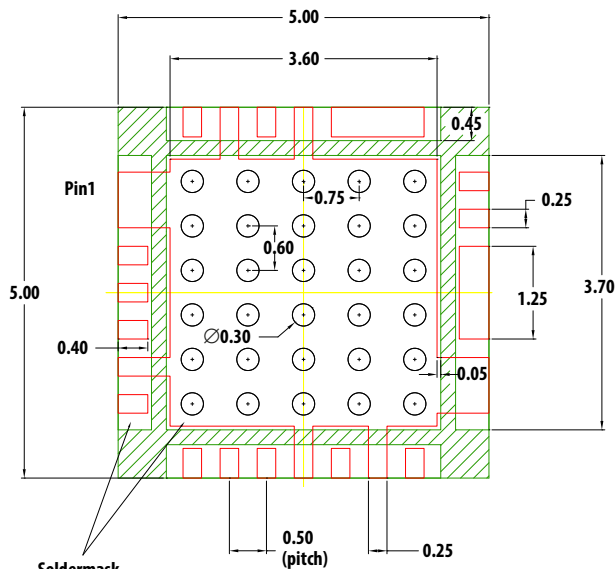
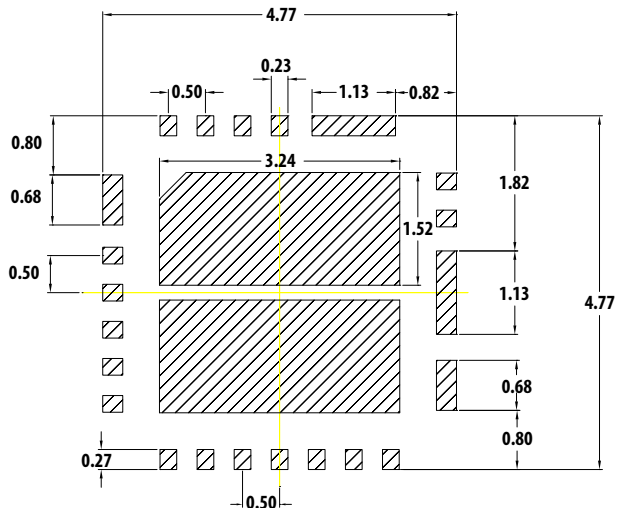


Figure 30. I_C vs. V_C at $V_{DD} = V_{DD\text{Bias}} = 5.5$ V

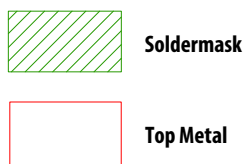
PCB Land Pattern and Stencil Outline



Land Pattern

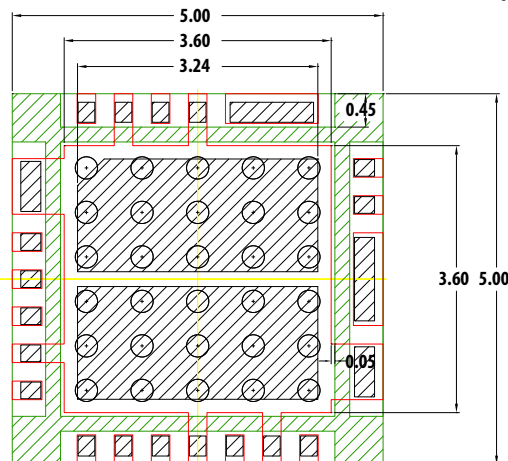


Stencil Opening



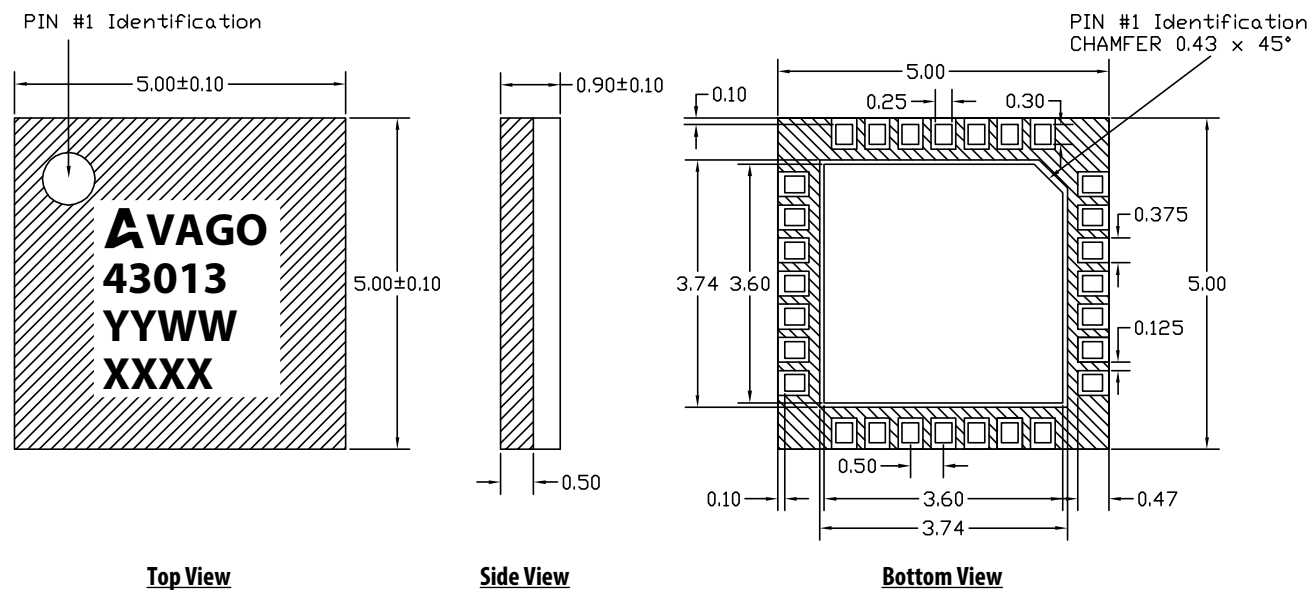
Notes:

1. Recommended Land Pattern and Stencil
2. 4 mils stencil thickness recommended
3. All dimensions are in mm



Combination of Land Pattern & Stencil Opening

MCOB (5.0 × 5.0 × 0.9) mm 28-Lead Package Dimensions



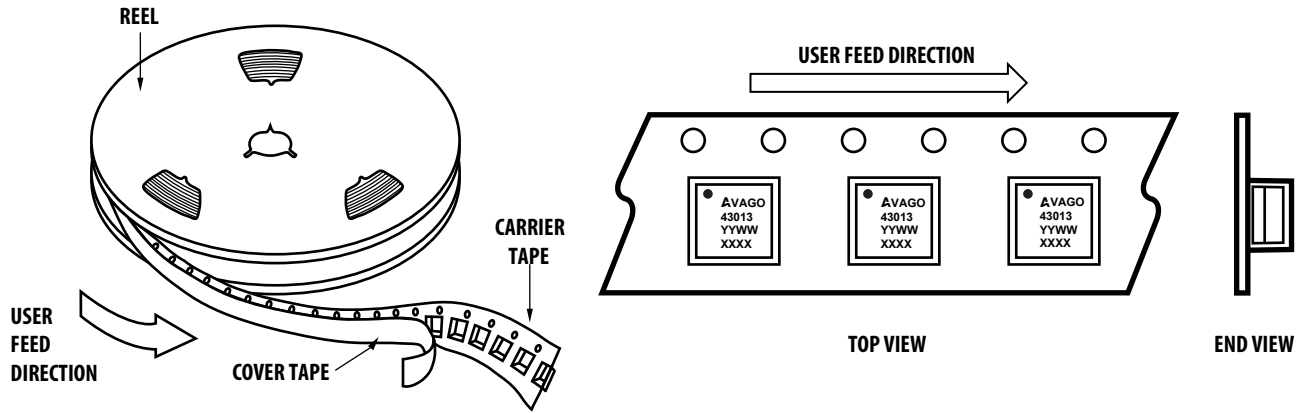
Notes:

1. All dimensions are in millimeters.
2. Dimensions are inclusive of plating.
3. Dimensions are exclusive of mold flash and metal burr.

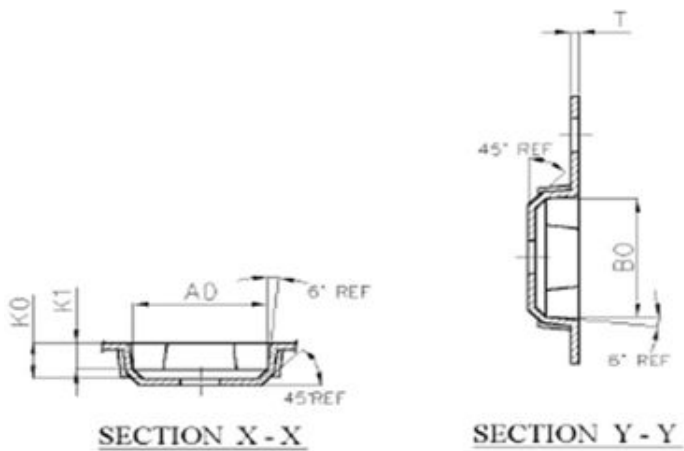
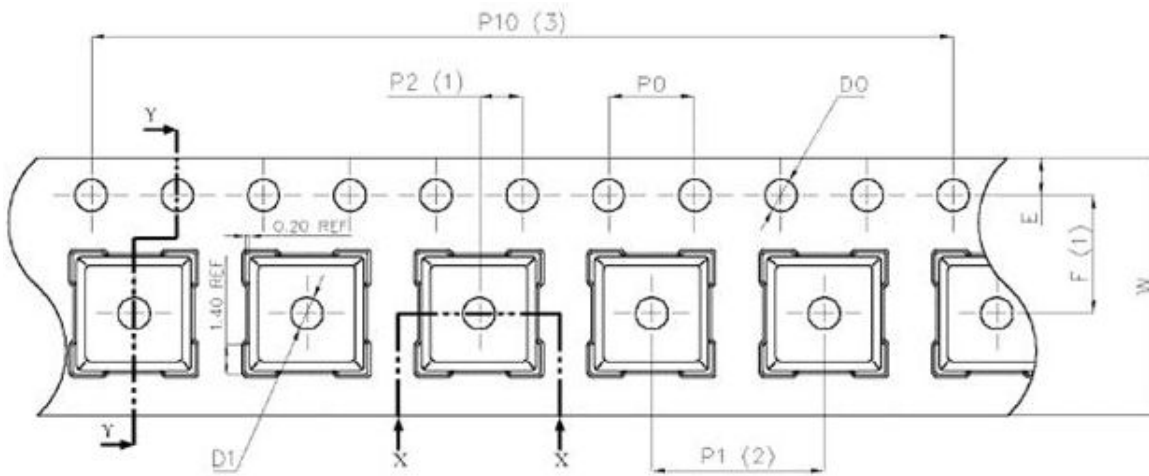
Part Number Ordering Information

Part Number	Qty	Container
MGA-43013-BLKG	100	Antistatic Bag
MGA-43013-TR1G	1000	7" Reel

Device Orientation

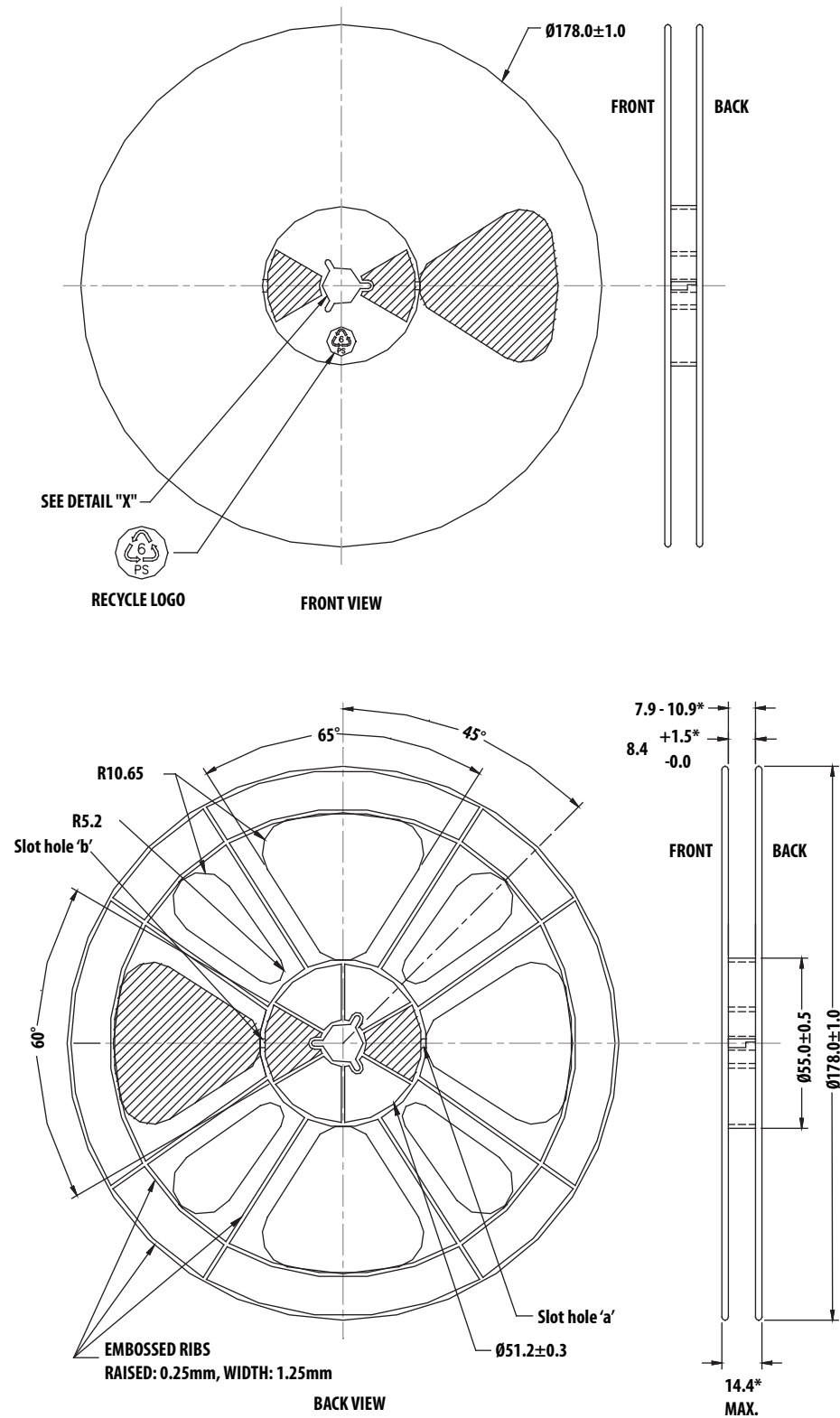


Tape Dimensions



Dimension List			
Annote	Millimeter	Annote	Millimeter
A0	5.40±0.10	P0	4.00±0.10
B0	5.40±0.10	P2	2.00±0.10
D0	1.50 ^{+0.10} ₀	P10	40.00±0.20
D1	1.60±0.10	E	1.75±0.10
K0	1.90±0.10	F	5.50±0.10
K1	1.50±0.10	T	0.30±0.03
P1	8.00±0.10	W	12.00±0.30

Reel Dimensions (7" reel)



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